

# **Long Term Trends In Packaging Technology**

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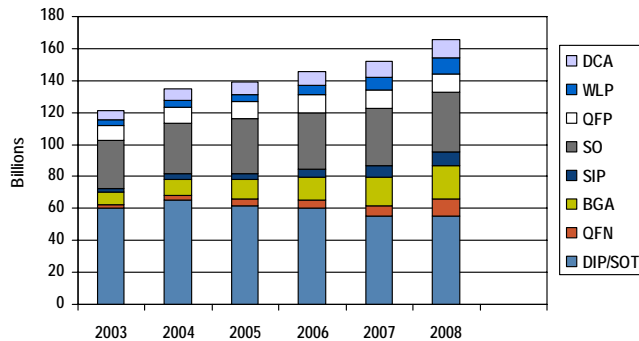
## **Major Packaging Industry Trends**

- Volume drivers have shifted to consumer electronics
- Longer term growth will be driven by machine to machine
- System In Package has become a mainstream technology
- Chip Scale Packages are beginning to replace older leadframe technologies due to cost, size, and performance advantages
- Wafer level packaging technologies is taking off
- The contract assembly and test business has started to consolidate driven by a more competitive environment
- The EMS and Assembly and Test overlaps are increasing
- Improvements in cost are not keeping pace with pricing pressure



## Shifts In Packaging Technology

World Wide Semiconductor Package Volume



Source: Electronic Trends Publications and Prismark



International Technology Roadmap for Semiconductors

## Difficult Challenges Near Term

- **Tools and methodologies to address chip and package co-design**
  - Mixed signal co-design and simulation (SI, Power, EMI)
  - For transient and localized hot spots - simulation of thermal mechanical stresses, thermal performance and current density in solder bumps
- **Close the Gap between chip and substrate interconnect density**
  - Increased wireability and dimensional control at low cost
  - Higher temperature stability and lower moisture absorption
  - TCE and Modulus better matched to low K flip chip requirements
- **Wafer Level Packaging**
  - I/O pitch between 250um 400um less than 100 I/O
  - Solder joint reliability and cleaning processes for low stand-off
  - Wafer thinning and handling technologies
  - Compact ESD structures
- **Impact of Cu/low k on Packaging**
  - Direct wire bond and UBM/bump to Cu to reduce cost
  - Lower TCE and modulus substrates to reduce die level stress in flip chip
  - Lower strength in low k which creates a weaker mechanical structure



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## Packaging Near Term Requirements

Year of Production	2004	2005	2006	2007	2008	2009
<i>Cost per Pin Minimum for Contract Assembly [1,2] (Cents/Pin)</i>						
Low-cost, hand-held and memory	0.30–53	.27–.50	.26–.48	.25–.45	.23–.43	.22–.41
Cost-performance	.71–1.24	.67–1.17	.64–1.11	.61–1.05	.58–1.00	.55–.96
High-performance	1.88	1.78	1.69	1.61	1.52	1.45
Harsh	0.32–2.88	0.29–2.60	0.26–2.33	0.25–2.11	0.23–2.00	0.22–1.90
<i>Chip Size (mm<sup>2</sup>) [3]</i>						
Low-cost	100	100	100	100	100	100
Cost-performance	140	140	140	140	140	140
High-performance	310	310	310	310	310	310
Harsh	100	100	100	100	100	100
<i>Maximum Power (Watts/mm<sup>2</sup>) [4]</i>						
Low-cost (Watts) [5]	2.7	2.8	3	3	3	3
Cost-performance	0.6	0.65	0.7	0.74	0.79	0.83
High-performance	0.51	0.54	0.58	0.61	0.64	0.64
Harsh	0.16	0.16	0.18	0.18	0.2	0.2
<i>Package Pincount Maximum [6][7]</i>						
Low-cost	122–500	134–550	144–600	160–660	180–720	180–800
Cost-performance	500–1600	550–1760	550–1936	600–2140	600–2400	660–2800
High-performance	3000	3400	3800	4000	4400	4600
Harsh	500	550	600	660	720	780



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## Packaging Near Term Requirements

Minimum Overall Package Profile (mm)	2004	2005	2006	2007	2008	2009
Low-cost	0.5	0.5	0.5	0.5	0.5	0.5
Cost-performance	0.8	0.8	0.8	0.8	0.65	0.65
High-performance	N/A	N/A	N/A	N/A	N/A	N/A
Harsh	0.8	0.8	0.8	0.8	0.8	0.8
<i>Performance: On-Chip (MHz) [8]</i>						
Low-cost	552/5200	607/3865	668/4251	735/4676	800/5000	830/5150
Cost-performance	3990	5170	5630	6740	—	—
High-performance	3990	5170	5630	6740	—	—
Harsh	80	88	96	106	116.6	128.26
<i>Performance: Chip-to-Board for Peripheral Buses (MHz) [9]</i>						
Low-cost	100	100	100	100	100	100
Cost-performance (for multi-drop nets)	533	600	667	733	800	800
High-performance (for differential-pair point-to-point nets)	2500	3125	3906	4883	6103	7629
Harsh	80	88	96	106	106	115



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## Die to Package Interconnect Requirements

<i>Year of Production</i>	2004	2005	2006	2007	2008	2009	2010	2012	2013	2015	2016	2018
Wire bond pitch - ball	40	35	35	30	30	25	25	25	25	25	25	25
Wire bond pitch -wedge	30	30	25	20	25	20	20	20	20	20	20	20
TAB*	35	30	30	25	25	25	20	20	20	15	15	15
Flip chip area array*	150	130	130	120	110	100	90	90	90	80	80	70
Peripheral flip chip Stud Bump	60	40	40	30	30	20	20	20	20	15	15	15

Note: Validation for 100 um pitch required



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## Package I/O Pitches

<i>Year of Production</i>	2004	2005	2006	2007	2008	2009	2010	2012	2013	2015	2016	2018
<i>BGA Solder Ball Pitch (mm)</i>												
Low-cost and hand-held	0.8	0.65	0.65	0.65	0.65	0.65	0.5	0.5	0.5	0.5	0.5	0.5
Cost-performance	0.8	0.65	0.65	0.65	0.65	0.65	0.5	0.5	0.5	0.5	0.5	0.5
High-performance	1	1	0.8	0.8	0.8	0.8	0.65	0.65	0.5	0.5	0.5	0.5
Harsh	0.8	0.8	0.8	0.65	0.65	0.65	0.65	0.5	0.5	0.5	0.5	0.5
<u>Chip Scale Package Pitch</u>	0.4	0.3	0.3	0.2	0.2	0.2	0.2	0.15	0.15	0.15	0.1	0.1



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## System In Package Roadmap

<i>System In Package Requirements</i>												
<i>Year of Production</i>	2004	2005	2006	2007	2008	2009	2010	2012	2013	2015	2016	2018
<i>Digital networks- max I/O</i>	2600	2900	3000	3200	3500	3500	3500	3500	3500	3500	3500	3500
<i>RF products - max I/O</i>	150	200	200	200	200	200	200	200	200	200	200	200
<i>Memory products - max I/O</i>												
<i>Max number of stack die</i>	6	7	8	8	8	8	8	8	8	8	8	8
<i>Max number die in Module</i>	10	12	12	12	12	12	12	12	12	12	12	12
<i>Minimum Component size in.</i>	0201	0201	01005	01005	01005	01005	01005	01005	01005	01005	01005	01005
<i>Die Pad pitch - wirebond</i>	40	35	35	30	30	25	25	25	25	25	25	25
<i>Die pad pitch - flipchip</i>	150	130	130	120	110	100	90	90	80	80	70	70
<i>Embedded Passives in Laminate</i>	L	L	CL	CL	CL	CL	CL	CL	CL	CL	CL	CL
<i>Embedded Passives in Ceramic</i>	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C	R, L, C, R, L, C
<i>MSL Level</i>	2a	2	2	2	2	2	2	2	2	2	2	2
<i>Mx Reflow temp C</i>	260	260	260	260	260	260	260	260	260	260	260	260



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## Materials Challenges

<i>Materials Challenges</i>	<i>Issues</i>
Wirebond	Materials that enable 20 micron pitch without wire sweep, barrier metals for Cu wirebond pads to reduce intermetallic
Underfills	Ability to support 100 pitch on large die, reduce stress on low K and compatibility with lead free reflow
Thermal Interfaces	Increased thermal conduction, improved adhesion, higher modulus for thin applications
Materials Properties	Methodology and characterization database for frequencies above 10 GHz,
Molding Compound	Low modulus materials that reduce stress on low-κ wafer structures with low moisture absorption for high temperature lead free applications
Leadfree Solder Flip Chip Materials	Solder and UBM the supports high current density and avoid electromigration
Die attach solder for Tj >200C	No feasible solution seen
Rigid Organic substrates	Lower loss dielectric, lower TCE, and higher Tg at low cost
Flexible Organic Substrates	Lower TCE and improved metal adhesion
Embedded passives	Improved high frequency performance of dielectrics with K above 1000 High reliability, better stability resistor materials. Ferromagnetics for sensor and MEMs applications
LTCC	Low shrink dielectric and lower dielectric constant for high frequency application



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## Conclusions

- The industry growth will be driven by consumer and machine to machine based applications going forward
- SIP and WLP technologies will be a key element of this growth and are shifting the industry research focus
- To improve R&D return and effectiveness the industry needs to increase collaboration through partnerships and shared R&D
- Emerging devices will required a new set of packaging technologies that allow devices to interact with the environment instead of being protected from it

